Power Transistor 15A

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Features:

- The 2N3055H is a Silicon power base transistor for high power audio, seriespass power supplies, disk-head positioners and other linear application. These devices can also be used in power switching circuits such as converters or inverters
- Higher safe operating area than 2N3055 at V_{CE} >40V
- · Low saturation voltages
- · High power dissipation capability

Maximum Ratings

Rating	Symbol	Rating	Unit	
Collector-Emitter Voltage	V _{CEO}	60		
Collector-Emitter Voltage	V _{CER}	70		
Collector-Base Voltage	V _{CBO}	100		
Emitter-Base Voltage	V _{EBO}	7		
Collector Current-Continuous	Ι _C	15		
Base Current	Ι _Β	7	A	
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	115 0.657	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +200	°C	

Thermal Characteristics

Characteristic	Symbol	Max.	Unit
Thermal Resistance Junction to Case	R _{ejc}	1.52	°C/W

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Characteristic	Symbol	Min.	Max.	Unit
OFF Characteristics (1)		^	·	
Collector-Emitter Sustaining Voltage $(I_C = 200 \text{mA}, I_B = 0)$	V _{CEO(sus)}	60	-	
Collector-Emitter Sustaining Voltage (I_C = 200mA, R_{BE} = 100 Ω)	V _{CER(sus)}	70	-	V
Collector-Emitter Sustaining Voltage ($I_C = 100$ mA, $V_{BE(off)} = 1.5V$)	V _{CEX(sus)}	90	-	
Collector Cut off Current ($V_{CE} = 30V$, $I_B = 0$)	I _{CEO}	-	0.7	
Collector Cut off Current ($V_{CE} = 100V$, $V_{BE(off)} = 1.5V$) ($V_{CE} = 100V$, $V_{BE(off)} = 1.5V$, $T_{C} = 150^{\circ}C$)	I _{CEX}	-	1 5	mA
Emitter Cut off Current ($V_{EB} = 7V$, $I_C = 0$)	I _{EBO}	-	5	
ON Characteristics				
DC Current Gain ($I_C = 4A$, $V_{CE} = 4V$) ($I_C = 10A$, $V_{CE} = 4V$)	h _{FE}	20 5	70	-
Collector-Emitter Saturation Voltage $(I_C = 4A, I_B = 0.4A) (I_C = 10A, I_B = 3.3A)$	V _{CE(sat)}	-	1.1 8	V
Base-Emitter on Voltage $(I_C = 4A, V_{CE} = 4V)$	V _{BE(on)}	-	1.8	
Second Breakdown				
Second Breakdown Collector Current with Base Forward Based (t = 1s (non-repetitive), $V_{CE} = 60V$)	I	800	-	kHz
Dynamic Characteristics				
Current Gain-Bandwidth Product (2) ($I_C = 1A, V_{CE} = 4V$)	f	800	-	kHz
Small-Signal Current Gain ($I_C = 1A$, $V_{CE} = 4V$, f = 1kHz)	h	10	-	-

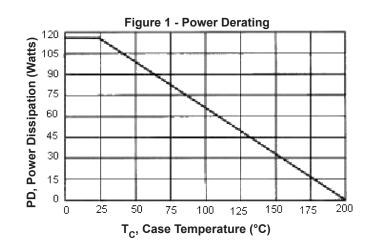
Electrical Characteristics ($T_c = 25^{\circ}C$ unless otherwise notes)

(1) Pulse Test : Pulse Width = 300µs, Duty Cycle ≤2% (2) $f_T = | hfe | \cdot f_{test}$

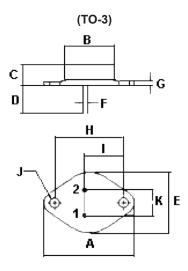
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Dimensions



Pin Configuration

- 1. Base
- 2. Emitter Collector (Case)

Dimensions	Min.	Max.
А	38.75	39.96
В	19.28	22.23
С	7.96	9.28
D	11.18	12.19
E	25.2	26.67
F	0.92	1.09
G	1.38	1.62
Н	29.9	30.4
I	16.64	17.3
J	3.88	4.36
К	10.67	11.18

Dimensions : Millimetres

Part Number Table

Description	Part Number	
NPN Silicon Transistors, 60V, 115W	2N3055H	

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